



40V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 40V
- I_C = 1A High Continuous Current
- I_{CM} = 2A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 500mV @ 1A
- Complementary PNP Type: FZT591A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

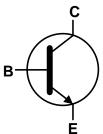
Applications

- Power MOSFET Gate Driving
- Low Loss Power Switching

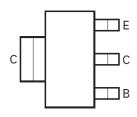
SOT223 (Type DN)







Device Symbol



Top View Pin-Out

Ordering Information (Note 5)

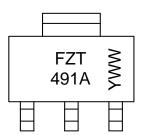
1-					
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT491ATA	AEC-Q101	FZT491A	7	12	1,000
FZT491AQTA	Automotive	FZT491A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223 (Type DN)



FZT 491A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 9 = 2019) WW or $\overline{W}W$ = Week Code (01 to 53)

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Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Base Current	Ι _Β	200	mA
Peak Pulse Current	I _{CM}	2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0		
Dower Dissipation	(Note 7)	<u> </u>	2.0	W	
Power Dissipation	(Note 8)	P_{D}	1.6		
	(Note 9)		1.2]	
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)	_	62.5		
Thermal Resistance, Junction to Ambient	(Note 8)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 9)		104	1	
Thermal Resistance Junction to Lead (Note 10)		$R_{ heta JL}$	19.4		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 11)

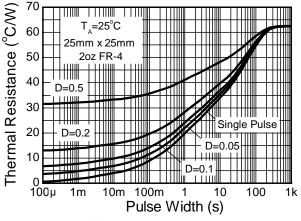
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

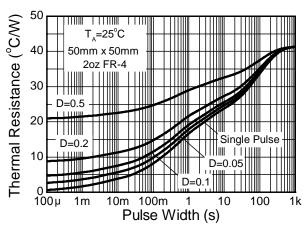
Notes:

- 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 10. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

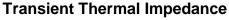


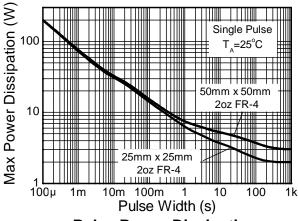
Thermal Characteristics and Derating Information

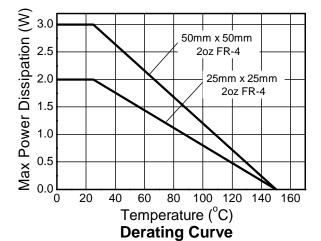




Transient Thermal Impedance







Pulse Power Dissipation

March 2019



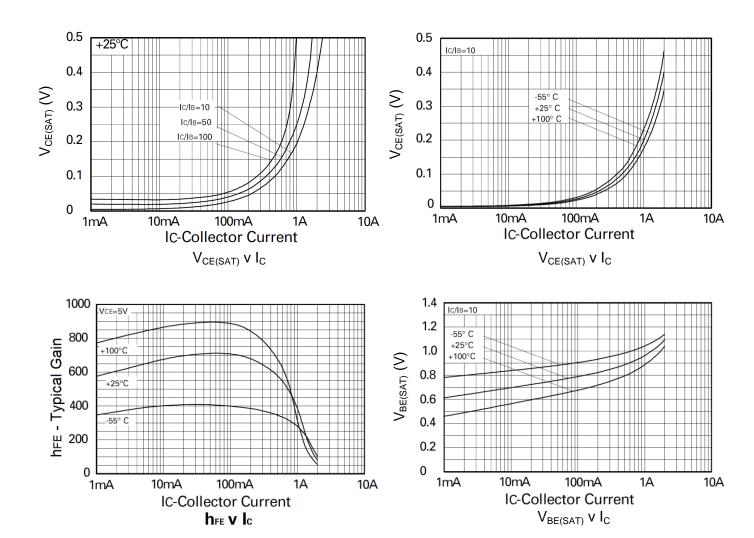
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

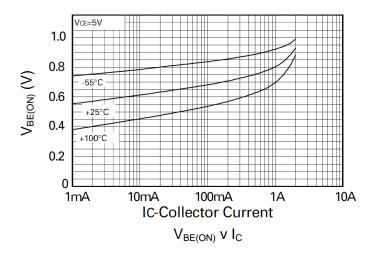
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	40	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	_	_	V	$I_E = 100\mu A$
Collector Cut-Off Current	I _{CBO}	_	_	100	nA	V _{CB} = 30V
Collector Cut-Off Current	I _{CES}	_	_	100	nA	V _{CES} = 30V
Emitter Cut-Off Current	I _{EBO}	_	_	100	nA	V _{EB} = 4V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(SAT)}	_	_	0.3	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 12)				0.5	V	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(SAT)}$	_	_	1.1	V	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn-On Voltage (Note 12)	$V_{BE(ON)}$	_	_	1.0	V	$I_C = 1A, V_{CE} = 5V$
		300	_	_		$I_C = 1mA$, $V_{CE} = 5V$
DC Current Gain (Note 12)	h	300	_	900		$I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$
DC Current Gain (Note 12)	h _{FE}	200	_	_	_	$I_{C} = 1A, V_{CE} = 5V$
		35	_	_		$I_C = 2A$, $V_{CE} = 5V$
Current Gain-Bandwidth Product	f⊤	150	_	_	MHz	$V_{CE} = 10V, I_{C} = 50mA$
Outront Gain Bandwidth Houdet	1	130				f = 100MHz
Output Capacitance	Сово	_	_	10	pF	$V_{CB} = 10V$, $f = 1MHz$

Note: 12. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



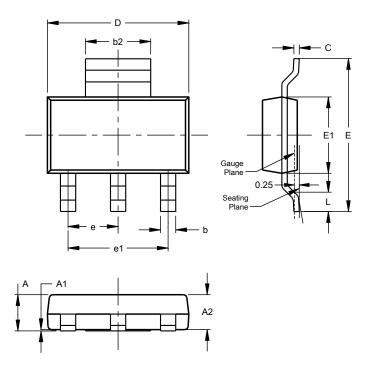




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

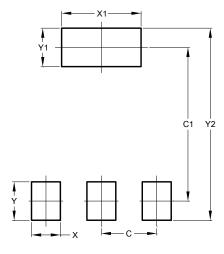


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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